

**LIST OF REFERENCES CITED BY
APPLICANT**
(REVISED FORM PTO-1449)
DATED: April 25, 1997

Applicant: Tomohiro Kawase et al.

U. S. Filing Date: April 25, 1997 Art Unit:**U. S. PATENT DOCUMENTS**

*EXAMINER INITIAL		DOCUMENT NO.							DATE	NAME	Cl.	Sub-Cl.	Fil. Date
ED		AA	4	9	9	9	0	8	2	3/91	Kremer et al.		

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.							DATE	COUNTRY	Cl.	Sub-Cl.	Trans.		
													Yes	No	
ED	AB	3-	2	5	2	3	9	9	11/1991	Japan					
ED	AC	2-		7	4	5	9	7	3/90	Japan					
ED	AD	64		7	9	0	8	7	3/89	Japan					

OTHER DOCUMENTS

ED 6/3/98	AE	Journal of Japanese Association of Crystal Growth, Y. Okabe et al. UNDOPED SEMI-INSULATING GaAs SINGLE CRYSTALS GROWN BY VGF METHOD, Vol. 18, 1991, pages 88 - 95

EXAMINER*Evelyn A. DeFillio***DATE CONSIDERED***Dec 31, 1997*

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant